Small Signal MOSFET

20 V, 238 mA, Single, N-Channel, Gate ESD Protection, SC-75

Features

- Low Gate Charge for Fast Switching
- Small 1.6 x 1.6 mm Footprint
- ESD Protected Gate
- Pb-Free Package is Available

Applications

- Power Management Load Switch
- Level Shift
- Portable Applications such as Cell Phones, Media Players,
 Digital Cameras, PDA's, Video Games, Hand Held Computers, etc.

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Paramo	Symbol	Value	Unit	
Drain-to-Source Voltage		V_{DSS}	20	V
Gate-to-Source Voltage	V _{GS}	±10	V	
Continuous Drain Current (Note 1)			238	mA
Power Dissipation (Note 1)	Steady State = 25°C	P _D	300	mW
Pulsed Drain Current $t_P \le 10 \mu s$		I _{DM}	714	mA
Operating Junction and St	T _J , T _{STG}	-55 to 150	°C	
Continuous Source Curre	I _{SD}	238	mA	
Lead Temperature for Sole (1/8" from case for 10 s)	T _L	260	°C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{\theta JA}$	416	°C/W

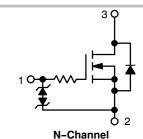
Surface-mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq. [1 oz] including traces).



ON Semiconductor®

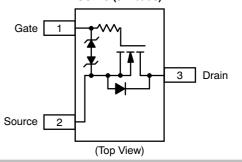
http://onsemi.com

V _{(BR)DSS}	R _{DS(on)} Typ @ V _{GS}	I _D MAX (Note 1)
20 V	1.5 Ω @ 4.5 V	238 mA
	2.2 Ω @ 2.5 V	

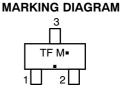


PIN CONNECTIONS

SC-75 (3-Leads)







TF = Specific Device Code

M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
NTA4001NT1	SC-75	3000 Tape & Reel
NTA4001NT1G	SC-75 (Pb-Free)	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	$V_{GS} = 0 \text{ V}, I_D = 100 \mu\text{A}$	20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 20 V			1.0	μΑ
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±10 V			±100	μΑ
ON CHARACTERISTICS (Note 2)						
Gate Threshold Voltage	V _{GS(TH)}	$V_{DS} = 3 \text{ V}, I_{D} = 100 \mu\text{A}$	0.5	1.0	1.5	V
Drain-to-Source On Resistance	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ mA}$		1.5	3.0	
		V _{GS} = 2.5 V, I _D = 10 mA		2.2	3.5	Ω
Forward Transconductance	9FS	$V_{DS} = 3 \text{ V}, I_{D} = 10 \text{ mA}$		80		mS
CAPACITANCES						
Input Capacitance	C _{ISS}	$V_{DS} = 5 \text{ V, f} = 1 \text{ MHz,} $ $V_{GS} = 0 \text{ V}$		11.5	20	
Output Capacitance	C _{OSS}			10	15	pF
Reverse Transfer Capacitance	C _{RSS}	143		3.5	6.0	
SWITCHING CHARACTERISTICS (Note 3)						-
Turn-On Delay Time	t _{d(ON)}			13		ns
Rise Time	t _r	V _{GS} = 4.5 V, V _{DS} = 5 V,		15		
Turn-Off Delay Time	t _{d(OFF)}	$I_D = 10 \text{ mA}, R_G = 10 \Omega$		98		ns
Fall Time	t _f			60		
DRAIN-SOURCE DIODE CHARACTERISTICS				-		
Forward Diode Voltage	V_{SD}	$V_{GS} = 0 \text{ V}, I_{S} = 10 \text{ mA}$		0.66	0.8	٧

Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
 Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

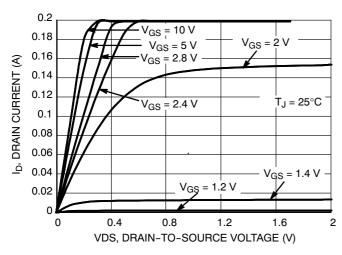


Figure 1. On-region Characteristics

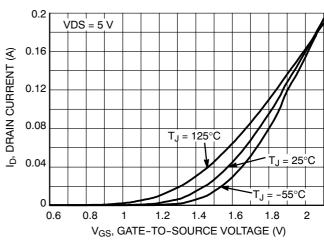


Figure 2. Transfer Characteristics

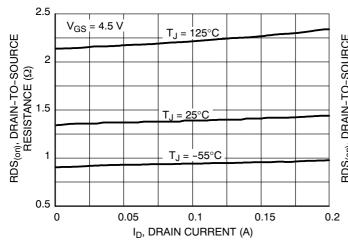


Figure 3. On-resistance versus Drain Current and Temperature

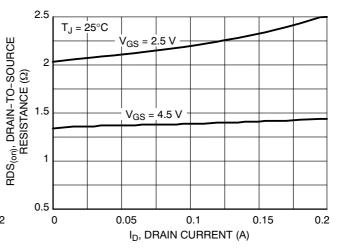


Figure 4. On-resistance versus Drain Current and Gate Voltage

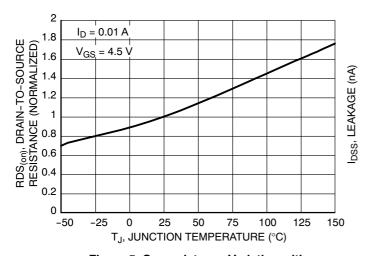


Figure 5. On-resistance Variation with Temperature

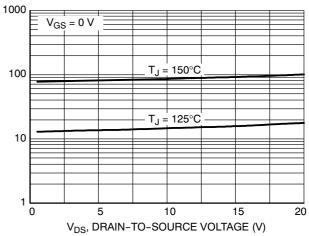
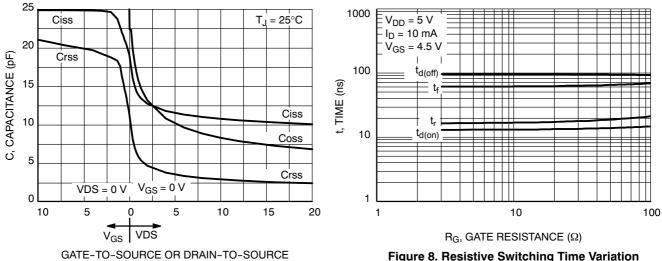


Figure 6. Drain-to-Source Leakage Current versus Voltage

TYPICAL PERFORMANCE CURVES



VOLTAGE (V)
Figure 7. Capacitance Variation

Figure 8. Resistive Switching Time Variation versus Gate Resistance

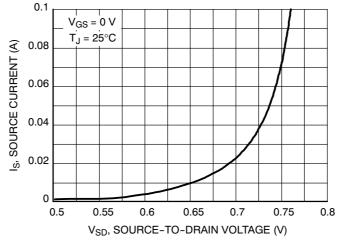
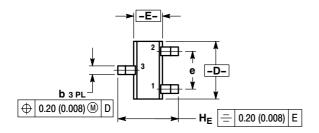
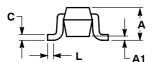


Figure 9. Diode Forward Voltage versus Current

PACKAGE DIMENSIONS

SC-75 / SOT-416 CASE 463-01 ISSUE F





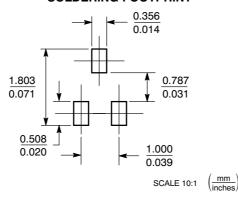
NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
 Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.70	0.80	0.90	0.027	0.031	0.035	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
b	0.15	0.20	0.30	0.006	0.008	0.012	
С	0.10	0.15	0.25	0.004	0.006	0.010	
D	1.55	1.60	1.65	0.059	0.063	0.067	
E	0.70	0.80	0.90	0.027	0.031	0.035	
е	1.00 BSC			0.04 BSC			
L	0.10	0.15	0.20	0.004	0.006	0.008	
HE	1.50	1.60	1.70	0.061	0.063	0.065	

STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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